

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3564	((INLET OUTLET) NEAR3 PORTION) WITH (GAS LIQUID) WITH CHAMBER	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 14:58
L2	1831	((INLET OUTLET) NEAR3 PORTION) WITH (GAS LIQUID) WITH CHAMBER.CLM.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 14:58
L3	49	((INLET OUTLET) NEAR3 PORTION) WITH (GAS LIQUID) WITH CHAMBER WITH CIRCULAR.CLM.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:23
L4	1	10/706415	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:33
L5	479	transistor with gate with ((si silicon) near3 containing)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:38
L6	96	5 and (dielectric with ((si silicon) near3 containing))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:39

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	U	I	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	-
49	P	r	US 20010051413	2001121		Spot-implant method for MOS transistor application	438/525			Wasshuber, Christoph	r	r	r	r	r	r
50	P	r	US 20010040255	2001111		SEMICONDUCTOR DEVICE HAVING NON	257/314	257/E29.1	65:	KOBAYASHI, TAKASHI et al.	r	r	r	r	r	r
51	P	r	US 20010021543	2001091		METHODS OF ENHANCING DATA RE	438/201	257/E21.6	82:	KELLER, J. DENNIS et al.	r	r	r	r	r	r
52	P	r	US 6864125 B2	2005030	8	Process for growing a dielectric layer on a silico	438/142	427/255.27		Sandhu; Gurtej Singh et al.	r	r	r	r	r	r
53	P	r	US 6844234 B2	2005011	8	Semiconductor device and method for manufact	438/287	438/591;		Eguchi; Kazuhiro et al.	r	r	r	r	r	r
54	P	r	US 6835983 B2	2004122	8	Silicon-on-insulator (SOI) integrated circuit (I	257/347	257/348;		Ning; Tak H. et al.	r	r	r	r	r	r
55	r	r	US 6821825 B2	2004112	33	Process for deposition of semiconductor films	438/150	117/88;		Todd; Michael A. et al.	r	r	r	r	r	r
56	r	r	US 6815296 B2	2004110	22	Polysilicon back-gated SOI MOSFET for dynam	438/283	257/347;		Dennard; Robert H. et al.	r	r	r	r	r	r
57	r	r	US 6812527 B2	2004110	20	Method to control device threshold of SOI MOSFE	257/347	257/348;		Dennard; Robert H. et al.	r	r	r	r	r	r
58	r	r	US 6808981 B2	2004102	23	Method for fabricating 6F2 trench DRAM cell w	438/243			Mandelman; Jack A. et al.	r	r	r	r	r	r
59	r	r	US 6790374 B1	2004091	12	Plasma etch method for forming plasma etched sil	216/37	134/1.1;		Ho; Kwok Keung Paul et al.	r	r	r	r	r	r
60	r	r	US 6777298 B2	2004081	22	Elevated source drain disposable spacer CMOS	438/301	438/303;		Roy; Ronnen A. et al.	r	r	r	r	r	r
61	r	r	US 6764902	2004072	28	Method of manufacturing	438/257	438/775:		Kobavashi; Takashi	r	r	r	r	r	r

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	U	1	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54	55	56	57	58	59	60	61	62	63	64	65	66	67	68	69	70	71	72	73	74	75	76	77	78	79	80	81	82	83	84	85	86	87	88	89	90	91	92	93	94	95																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																													
83	P	r	US 6379575	2002043	16	Treatment of etching chambers using activated	216/67	134/1.1;		Yin; Gerald Zheyao et al.	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r	r